

ABSTRACT

An organic thin film transistor of the present invention includes a substrate (11) and a semiconductor layer (14) made of an organic semiconductor and formed on the substrate (11). The semiconductor layer (14) is composed of crystals of the organic semiconductor, and a crystal phase of the crystals is the same as a crystal phase of energetically most stable bulk crystals of the organic semiconductor. A method for manufacturing the organic thin film transistor of the present invention includes forming the semiconductor layer (14) by depositing an organic semiconductor on the substrate (11). The organic semiconductor is deposited at a deposition rate of 0.1 to 1 nm/min while maintaining the temperature of the substrate (11) in the range of 40 to 150°C.